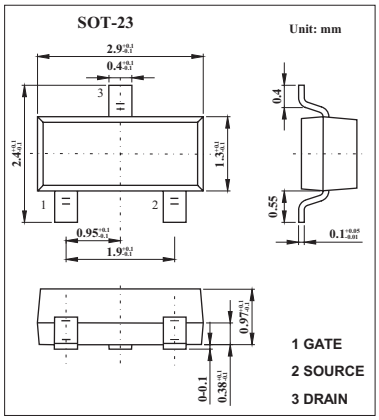
MOS Fied Effect Transistor

2SJ210



Features

- Directly driven by Ics having a 5V poer supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the biasresistor.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage V_{GS}=0	V_{DSS}	-60	V
Gate to source voltage V_{DS}=0	V_{GSS}	±20	V
Drain current (DC)	I_D	±200	m A
Drain current(pulse) *	I_D	±400	m A
Power dissipation	P_D	200	m W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW ⩽ 10 ms; d ⩽ 50%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	V_{DS}=-60V,V_{GS}=0			-10	μA
Gate leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0			±10	μA
Gate cut-off voltage	$V_{GS(off)}$	V_{DS}=-5.0V,I_D=-1μA	-1.4	-1.8	-2.4	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS}=-5.0V,I_D=-10mA	20	45		ms
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.0V,I_D=-10mA		10	15	Ω
		V_{GS}=-10V,I_D=-10mA		6	10	Ω
Input capacitance	C_{iss}	V_{DS}=-5.0V,V_{GS}=0,f=1MHZ		27		pF
Output capacitance	C_{oss}			21		pF
Reverse transfer capacitance	C_{rss}			3		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(on)}$=-4V,R_G=10Ω,V_{DD}=-5V,I_D=-10mA R_L=500Ω		120		ns
Rise time	t_r			190		ns
Turn-off delay time	$t_{d(off)}$			150		ns
Fall time	t_f			180		ns

Marking

Marking	H16